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Schematic diagram

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NCE2030K

XXXXX

Marking and pin assignment

TO-252-2L top view

NCE

(1) GO

NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE2030K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- V_{DS} =20V,I_D =30A
 - $\begin{aligned} R_{DS(ON)} <& 12m\Omega @ V_{GS} = 10V & (Typ:10.5m\Omega) \\ R_{DS(ON)} <& 13m\Omega @ V_{GS} = 4.5V & (Typ:11m\Omega) \\ R_{DS(ON)} <& 18m\Omega @ V_{GS} = 2.5V & (Typ:14m\Omega) \end{aligned}$
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Load switching
- Uninterruptible power supply

100% UIS TESTED!

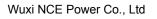
100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE2030K	NCE2030K	TO-252-2L	-	-	-

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	20	V	
Gate-Source Voltage	Vgs	±12	V	
Drain Current-Continuous	Ι _D	30	А	
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	21	А	
Pulsed Drain Current	I _{DM}	100	А	
Maximum Power Dissipation	PD	40	W	
Single pulse avalanche energy (Note 5)	E _{AS}	150	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	
Thermal Characteristic				
Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	3.8	°C/W	





Electrical Characteristics (T_A=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Off Characteristics	·	•				
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250µA	0.5	0.7	1.2	V
		V _{GS} =10V, I _D =20A	-	10.5	12	mΩ
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.5V, I _D =20A	-	11	13	mΩ
		V _{GS} =2.5V, I _D =20A	-	14	18	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =20A	10	-	-	S
Dynamic Characteristics (Note4)	·	•				
Input Capacitance	C _{lss}	V _{DS} =10V,V _{GS} =0V,		1544		PF
Output Capacitance	C _{oss}	F=1.0MHz		210.1		PF
Reverse Transfer Capacitance	C _{rss}			201.4		PF
Switching Characteristics (Note 4)		·				
Turn-on Delay Time	t _{d(on)}		-	4.5	-	nS
Turn-on Rise Time	tr	V _{GS} =10V,V _{DS} =10V	-	9.2	-	nS
Turn-Off Delay Time	t _{d(off)}	$R_L=0.5\Omega, R_{GEN}=3\Omega$	-	18.7	-	nS
Turn-Off Fall Time	t _f		-	3.3	-	nS
Total Gate Charge	Qg			23.5		nC
Gate-Source Charge	Q _{gs}	V _{GS} =4.5V,V _{DS} =10V,I _D =20A		2.8		nC
Gate-Drain Charge	Q _{gd}			5.75		nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	30	А
Reverse Recovery Time	trr	T _J = 25°C, I _F = 20A	-	18	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	9.5	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production

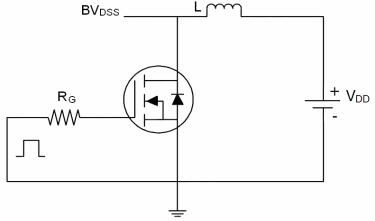
5. EAS condition: Tj=25 $^\circ \!\! \mathbb{C}, V_{DD} \!\! = \! 10V, V_G \!\! = \! 10V, L \!\! = \! 0.5mH, Rg \!\! = \! 25\Omega$



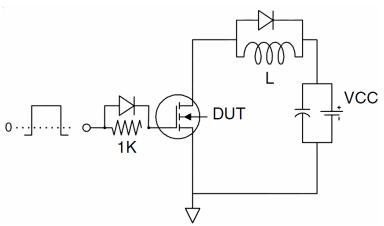
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Test circuit

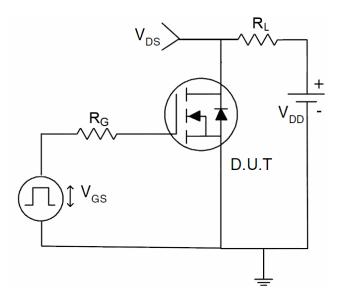
1) E_{AS} test Circuits



2) Gate charge test Circuit:

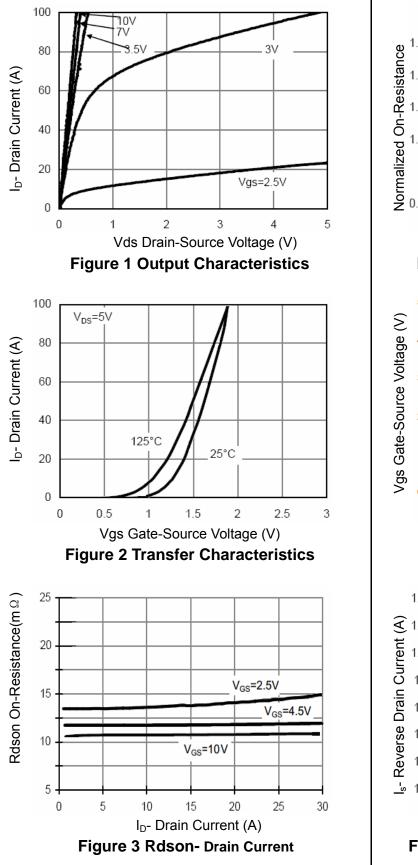


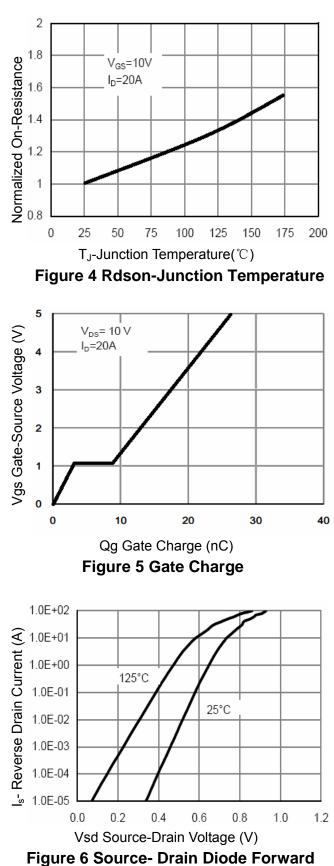
3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

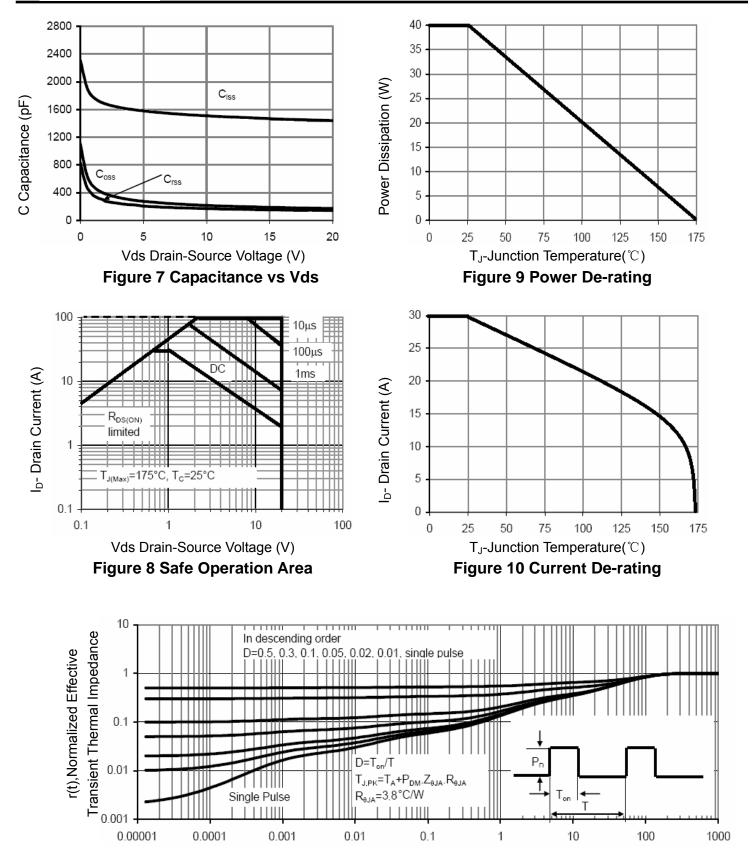






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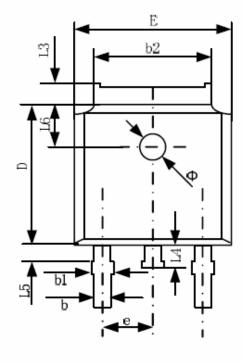
NCE2030K

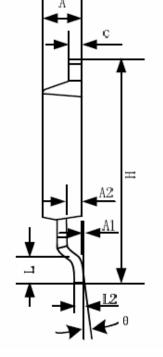


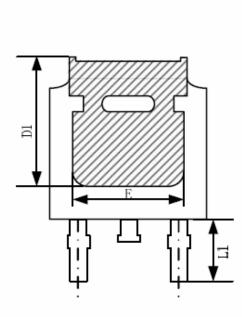
Square Wave Pluse Duration(sec) Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information







Cumahal	Dimensions	s In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	2.20	2.38	0.087	0.094	
A1	0.00	0.10	0.000	0.004	
A2	0.90	1.10	0.035	0.043	
b	0.72	0.85	0.028	0.033	
b1	0.72	0.90	0.028	0.035	
b2	5.13	5.46	0.202	0.215	
с	0.47	0.60	0.019	0.024	
D	6.00	6.20	0.236	0.244	
D1	5.25		0.207		
E	6.50	6.70	0.256	0.264	
E1	4.70		0.185		
e	2.19	2.39	0.086	0.094	
н	9.80	10.40	0.386	0.409	
L	1.40	1.70	0.055	0.067	
L1	2.90 REF		0.114 REF		
L2	0.508 BSC		0.020 BSC		
L3	0.90	1.25	0.035	0.049	
L4	0.60	1.00	0.024	0.039	
L5	0.15	0.75	0.006	0.030	
L6	1.80 REF		0.071 REF		
Φ	1.20	1.40	0.047	0.055	
θ	0°	8°	0°	8°	



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